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Photographs

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Photographs

1) Registration

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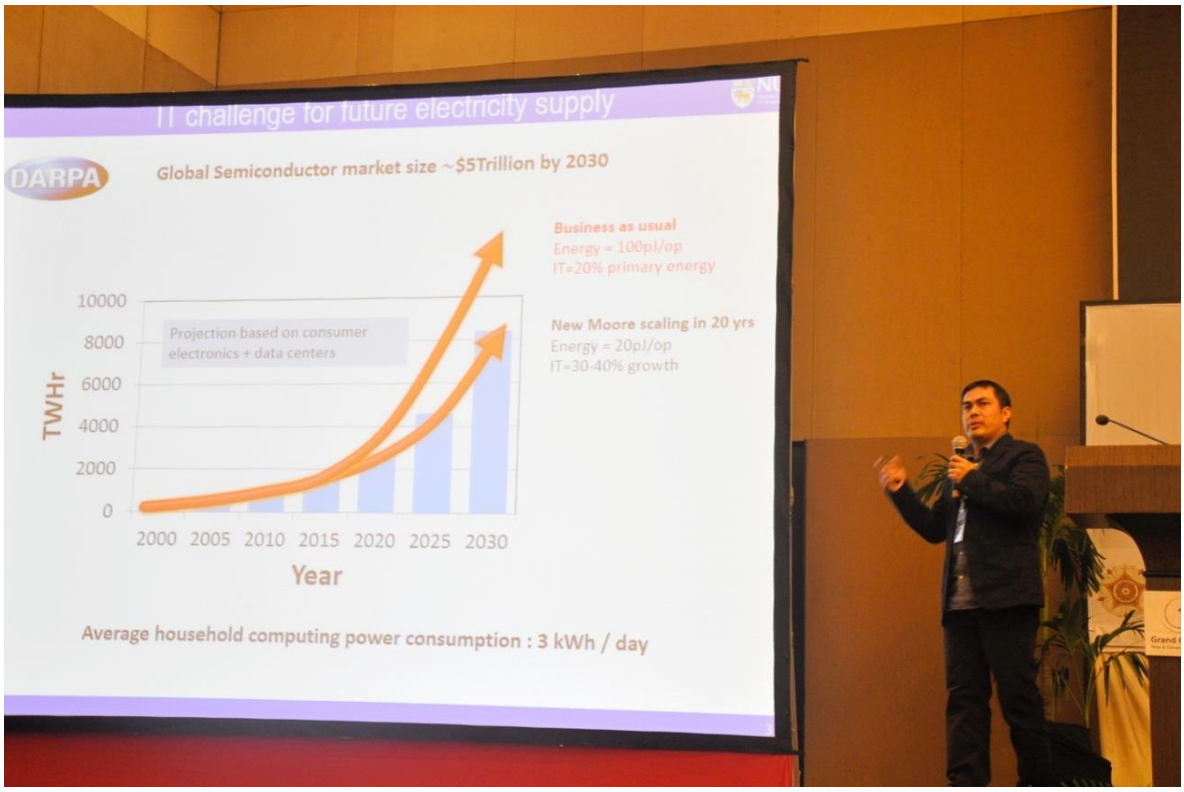
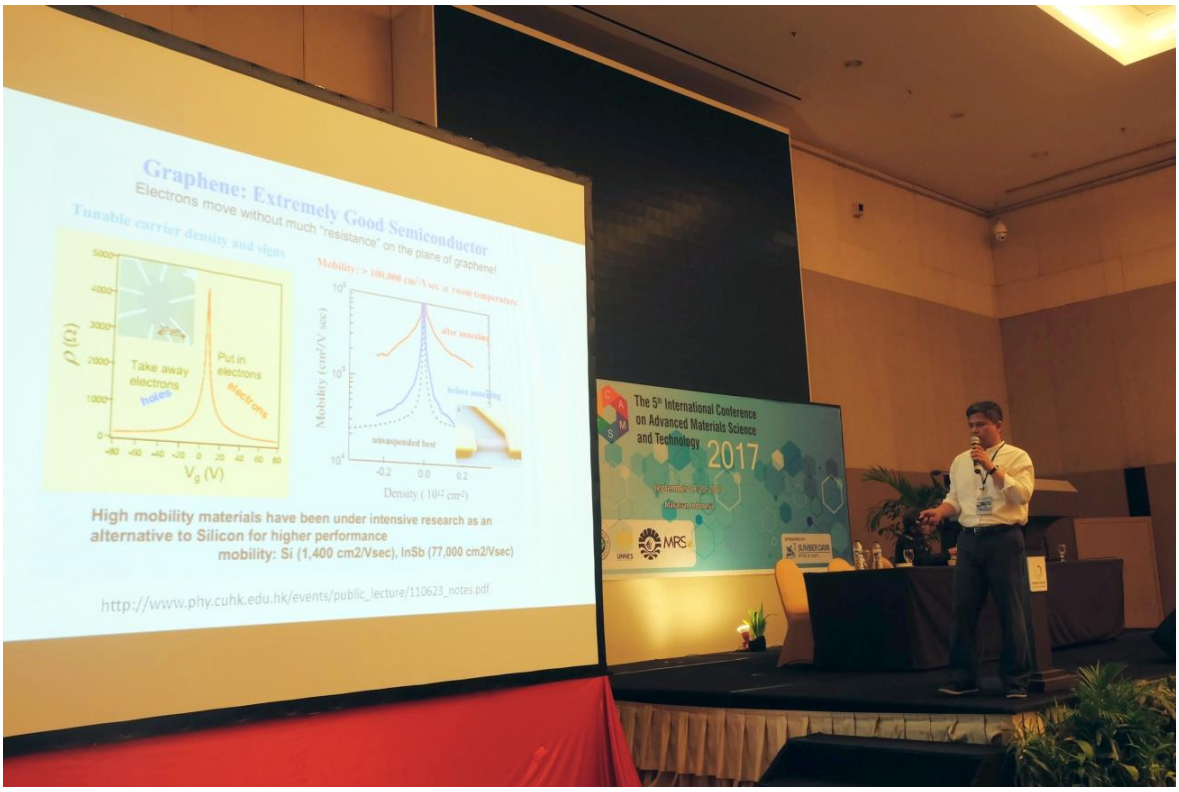
2) Open Ceremony

3) Photo Session

4) Plenary Session



5) Presentation



Experimental Procedure
Substrate : n-Si(100)
RCA Cleaning
Thermal Oxidation
2.5 - 10nm
2% O2 in N2
1000˚C
0.1%HF
Si-QDs Formation (LPCVD)
pure SiH4
560˚C
67Pa
Si-QD
Areal dot density : ~2x10^11 cm^-2
Selective Ge LPCVD (Ge core)
5% GeH4 in He
450˚C
2.7Pa
to be Ge core
Selective Si LPCVD (Si cap)
pure SiH4
560˚C
2.7Pa
Si-cap
Radical Oxidation
remote O2 plasma
1% O2 in He
560˚C
13Pa
PL Measurements @ RT~77K
900-1300nm: PMT
Excitation: 690nm, ~1.4W/cm
1300-2200nm: PbS
Excitation: 979nm, 4~20W/cm
Si (100)
The 5th International Conference on Advanced Materials Science and Technology

The 5th International Conference on Advanced Materials Science and Technology
2017
September 19-20, 2017
Makassar, Indonesia
MRS
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6) Participants

7) Parallel Session

Conclusion

8) Posters Session